

Списък на забелязаните цитати

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- (1) Terziyska, P., C. Blanc, J. Pernot, H. Peyre, S. Contreras, G. Bastide, J. Robert, J. Camassel, E. Morvan, C. Dua and C. Brylinski, "Evaluation of MESFET structures from temperature-dependent Hall effect measurements." *physica status solidi (a)* 195(1): 243-247 (2003).

Cited in:

1. Stefanakis, D. and K. Zekentes (2014). "TCAD models of the temperature and doping dependence of the bandgap and low field carrier mobility in 4H-SiC." *Microelectronic Engineering* 116: 65-71.
2. Στεφανάκης, Δ. Ζ. (2013). "Προσομοίωση JFET καρβιδίου πυριτίου με το TCAD εργαλείο της SILVACO."
3. Raoult, J., F. Pascal and C. Leyris (2010). "I-V and low frequency noise characterization of poly and amorphous silicon Ti-and Co-salicide resistors." *Thin Solid Films* 518(9): 2497-2500.
4. Deen, M. J. and F. Pascal (2006). "Electrical characterization of semiconductor materials and devices—review." *Journal of Materials Science: Materials in Electronics* 17(8): 549-575.
5. Deen, M. and F. Pascal (2006). Electrical characterization of semiconductor materials and devices. *Springer Handbook of Electronic and Photonic Materials*, Springer: 409-438.
6. Springer Handbook of Electronic and Photonic Materials, edited by Safa Kasap, Peter Capper, 2007.

- (1) Milanova, M. and P. Terziyska, "Low-temperature liquid-phase epitaxy growth from Ga–As–Bi solution." *Thin solid films* 500(1): 15-18 (2006).

Cited in:

1. You, X. and R. Zhou (2014). "Electronic Structure and Optical Properties of Alloy." *Advances in Condensed Matter Physics* 2014.
2. Habchi, M., I. Massoudi, A. Rebey, R. B. Chaâbane and B. El Jani (2014). "Analysis of the VIS-NIR spectral reflectance of Bi/GaAs structures grown by MOVPE and UHVE." *Journal of Crystal Growth* 395: 26-30.
3. Ding, L., P. Lu, H. Cao, N. Cai, Z. Yu, T. Gao and S. Wang (2013). "Bismuth alloying properties in GaAs nanowires." *Journal of Solid State Chemistry* 205: 44-48.
4. Graf, N. J. H. (2008). *Molekularstrahlepitaxie in den Mischsystemen Ga (Sb, Bi) und In (Sb, Bi)*.

- (2) Butcher, K. S. A., D. Alexandrov, P. Terziyska, V. Georgiev, D. Georgieva and P. W. Binsted, "InN grown by migration enhanced afterglow (MEAglow)." *physica status solidi (a)* 209(1): 41-44 (2012).

Cited in:

1. Haider, A., S. Kizir and N. Biyikli (2016). "Low-temperature self-limiting atomic layer deposition of wurtzite InN on Si (100)." *AIP Advances* 6(4): 045203.
2. Seidlitz, D., M. Senevirathna, Y. Abate, A. Hoffmann and N. Dietz (2015). Optoelectronic and structural properties of InGaN nanostructures grown by plasma-assisted MOCVD. *SPIE Optical Engineering+ Applications, International Society for Optics and Photonics*.
3. Gergova, R. *Growth and characterization of group III-nitrides by migration-enhanced afterglow epitaxy, Department of Chemistry, Lakehead University, PhD thesis* (2014).

4. Watson, I. M. (2013). "Metal organic vapour phase epitaxy of AlN, GaN, InN and their alloys: A key chemical technology for advanced device applications." *Coordination Chemistry Reviews* 257(13): 2120-2141.
 5. Seidlitz, D., M. Senevirathnaa, Y. Abatea, A. Hoffmannb and N. Dietza "Optoelectronic and structural properties of InGaN grown by Migration-Enhanced, Plasma-Assisted MOCVD." *Growth* 750: 800.
- (3) Butcher, K. S. A., D. Alexandrov, P. Terziyska, V. Georgiev and D. Georgieva, "Initial experiments in the migration enhanced afterglow growth of gallium and indium nitride." *physica status solidi (c)* 9(3-4): 1070-1073 (2012).
- Cited in:*
1. Gergova, R. *Growth and characterization of group III-nitrides by migration-enhanced afterglow epitaxy*, Department of Chemistry, Lakehead University, PhD thesis (2014).
 2. Binsted, P. W. *Gallium Nitride, Indium Nitride, and*, Lakehead University, PhD thesis (2014).
 3. Vodopyanov, A., D. Mansfeld, Y. Buzynin, M. Drozdov, Y. Drozdov, O. Khrykin, A. Lukyanov, M. Viktorov, S. Golubev and V. Shashkin (2013). "Indium Nitride Film Growth by Metal Organic Chemical Vapor Deposition with Nitrogen Activation in Electron Cyclotron Resonance Discharge Sustained by 24 GHz Gyrotron Radiation." *Japanese Journal of Applied Physics* 52(8S): o8JD07.
- (4) Terziyska, P. T., K. S. A. Butcher and D. Alexandrov, "Investigation of the presence of metal droplets after pulsed InN and GaN epitaxial growth using atomic force microscopy and nanoindentation." *Applied Surface Science* 258(24): 9997-10001 (2012).
- Cited in:*
1. Bao, K., W. Liu, A. Wang, X. Liu, R. Guo and Y. Wu (2012). "Shape-controlled synthesis of GaN microrods by ammonolysis route." *Applied Surface Science* 263: 682-687.
- (5) Butcher, K. S. A., B. W. Kemp, I. B. Hristov, P. Terziyska, P. W. Binsted and D. Alexandrov, "Gallium Nitride Film Growth Using a Plasma Based Migration Enhanced Afterglow Chemical Vapor Deposition System." *Japanese Journal of Applied Physics* 51(1S): o1AF02 (2012).
- Cited in:*
1. Wu, C., J. Wang, W. Zhang and Y. Luo (2015). "Modeling and simulation of ion-filtered inductively coupled plasma using argon plasma." *Japanese Journal of Applied Physics* 54(3): o36101.
 2. Ozgit-Akgun, C., E. Goldenberg, A. K. Okyay and N. Biyikli "Hollow cathode plasma-assisted atomic layer deposition of crystalline AlN, GaN and Al_xGa_{1-x}N thin films at low temperatures." *Journal of Materials Chemistry C* 2(12): 2123-2136 (2014).
 3. Gergova, R. *Growth and characterization of group III-nitrides by migration-enhanced afterglow epitaxy*, Department of Chemistry, Lakehead University, PhD thesis (2014).
- (6) Milanova, M., P. Vitanov, P. Terziyska, G. Popov and G. Koleva, "Structural and electrical characteristics of InGaAsN layers grown by LPE." *Journal of Crystal Growth* 346(1): 79-82 (2012).
- Cited in:*
1. Ashery, A. and A. Farag, "Fabrication, structural and electrical characterization of AlNi₂Si based heterojunction grown by LPE." *Materials Science in Semiconductor Processing* 35: 66-74 (2015).
- (7) Terziyska, P. T., K. S. A. Butcher, D. Gogova, D. Alexandrov, P. Binsted and G. Wu "InN nanopillars grown from In-rich conditions by migration enhanced afterglow technique." *Materials Letters* 106: 155-157, (2013).

Cited in:

1. Kamimura, J., M. Ramsteiner, U. Jahn, C.-Y. J. Lu, A. Kikuchi, K. Kishino and H. Riechert, "High-quality cubic and hexagonal InN crystals studied by micro-Raman scattering and electron backscatter diffraction." *Journal of Physics D: Applied Physics* 49(15): 155106 (2016).
2. Chauhan, A. K. S., M. Kumar and G. Gupta, "Catalyst free self-assembled growth of InN nanorings on stepped Si (553) surface." *Applied Surface Science* 345: 156-161 (2015).
3. Gergova, R. (2014). *Growth and characterization of group III-nitrides by migration-enhanced afterglow epitaxy*, Department of Chemistry, Lakehead University. (PhD thesis)

Докторска дисертация:

- (1) Terziyska, Penka. Propriétés de transport de α -SiC: application aux composants électroniques, Université des Sciences et Techniques du Languedoc Montpellier 2, (2003).

Cited in:

1. Blanqué, S. *Optimisation de l'implantation ionique et du recuit thermique pour SiC*, Universitat Autònoma de Barcelona, (2004).

Общ брой на намерените цитати: 27